

## P-Channel 1.5 V (G-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 8	0.023 at V <sub>GS</sub> = - 4.5 V	- 7	28
	0.029 at V <sub>GS</sub> = - 2.5 V	- 6.2	
	0.036 at V <sub>GS</sub> = - 1.8 V	- 5.2	
	0.048 at V <sub>GS</sub> = - 1.5 V	- 5.0	

### FEATURES

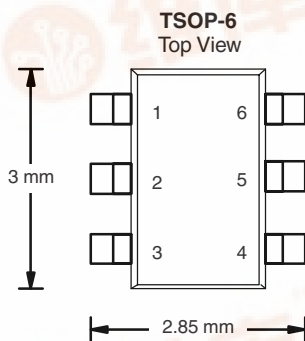
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET: 1.5 V Rated
- Ultra-Low On-Resistance
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



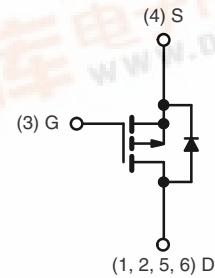
**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**  
 Available

### APPLICATIONS

- Load Switch for Portable Devices



**Ordering Information:** Si3499DV-T1-E3 (Lead (Pb)-free)  
 Si3499DV-T1-GE3 (Lead (Pb)-free and Halogen-free)  
**Marking Code:** B3xxx



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 8		V	
Gate-Source Voltage	V <sub>GS</sub>	± 5			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	- 7	- 5.3	A
		T <sub>A</sub> = 85 °C	- 3.6	- 3.9	
Pulsed Drain Current	I <sub>DM</sub>	- 20			
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	- 1.7	- 0.9		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	2.0	1.1	W
		T <sub>A</sub> = 85 °C	1.0	0.6	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	R <sub>thJA</sub>	45	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	25	30	

Notes:  
 a. Surface Mounted on 1" x 1" FR4 board.



SPECIFICATIONS $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.35		-0.75	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 5\ \text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -8\ \text{V}, V_{GS} = 0\ \text{V}$			-1	$\mu\text{A}$
		$V_{DS} = -8\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	-20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -7\ \text{A}$		0.019	0.023	$\Omega$
		$V_{GS} = -2.5\ \text{V}, I_D = -6.2\ \text{A}$		0.024	0.029	
		$V_{GS} = -1.8\ \text{V}, I_D = -5.2\ \text{A}$		0.028	0.036	
		$V_{GS} = -1.5\ \text{V}, I_D = -3\ \text{A}$		0.035	0.048	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\ \text{V}, I_D = -7\ \text{A}$		28		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.7\ \text{A}, V_{GS} = 0\ \text{V}$		-0.63	-1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -4\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -7\ \text{A}$		28	42	nC
Gate-Source Charge	$Q_{gs}$			2.9		
Gate-Drain Charge	$Q_{gd}$			5.8		
Gate Resistance	$R_g$		4	8.5	13	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\ \text{V}, R_L = 4\ \Omega$ $I_D = -1\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_g = 6\ \Omega$		27	40	ns
Rise Time	$t_r$			65	100	
Turn-Off Delay Time	$t_{d(off)}$			210	315	
Fall Time	$t_f$			110	165	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = -1.7\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		40	

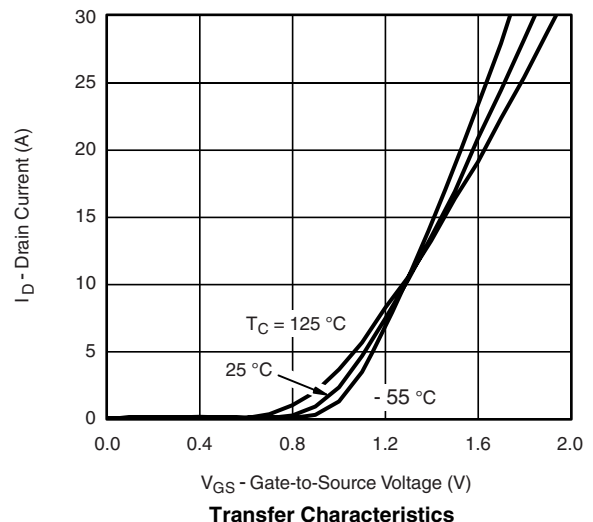
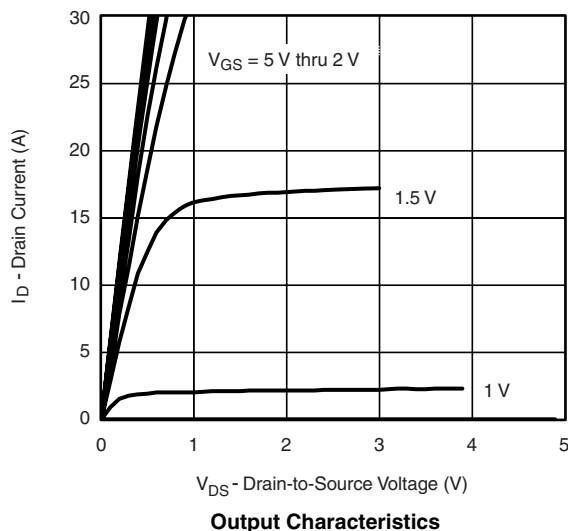
Notes:

a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

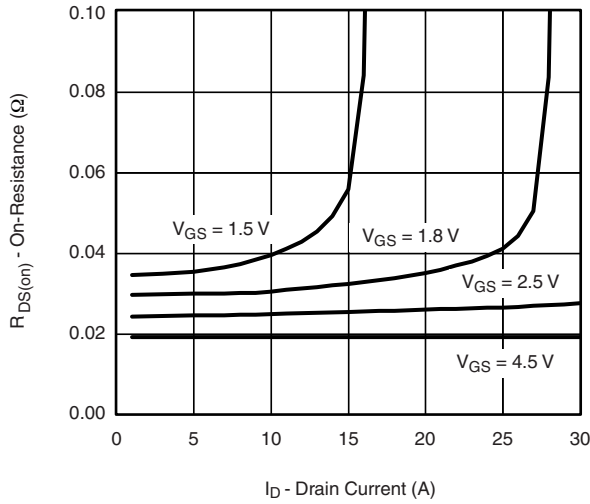
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

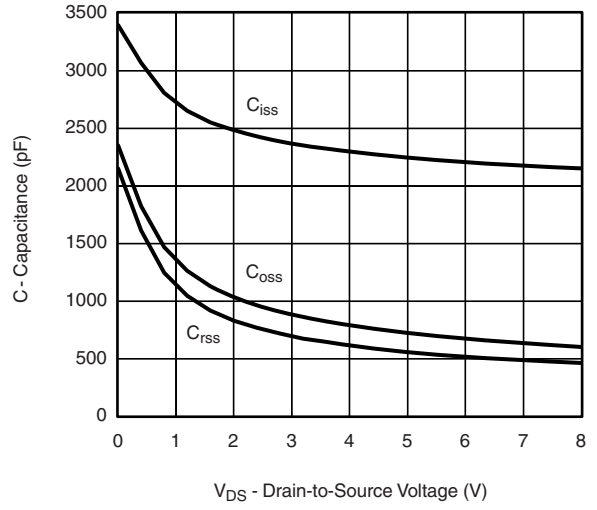
## TYPICAL CHARACTERISTICS $25^\circ\text{C}$ , unless otherwise noted



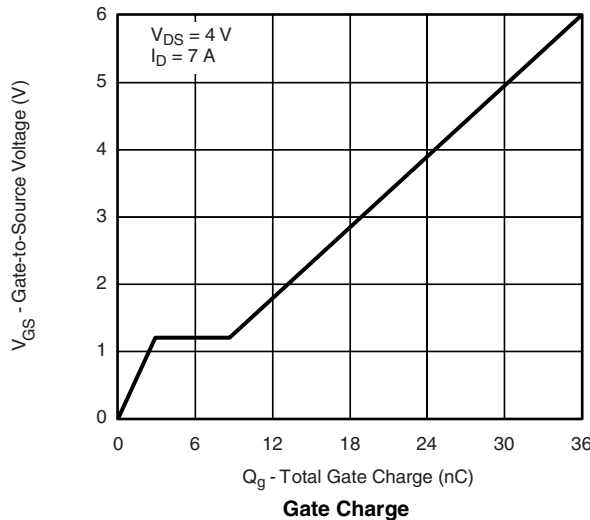
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



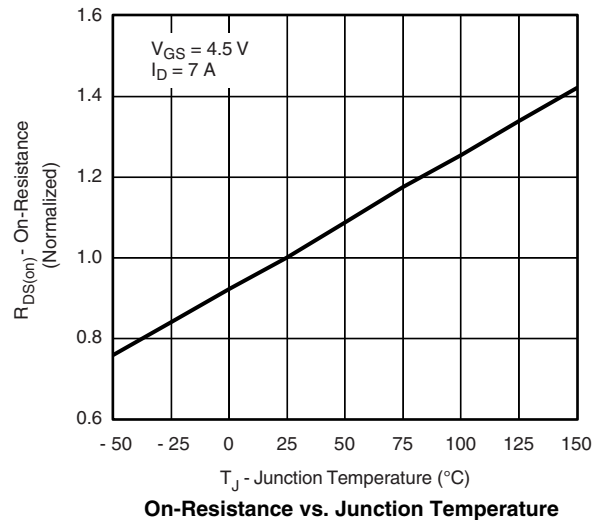
**On-Resistance vs. Drain Current**



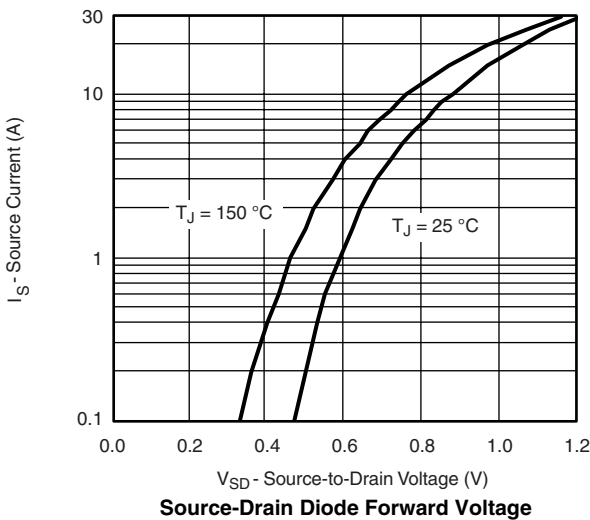
**Capacitance**



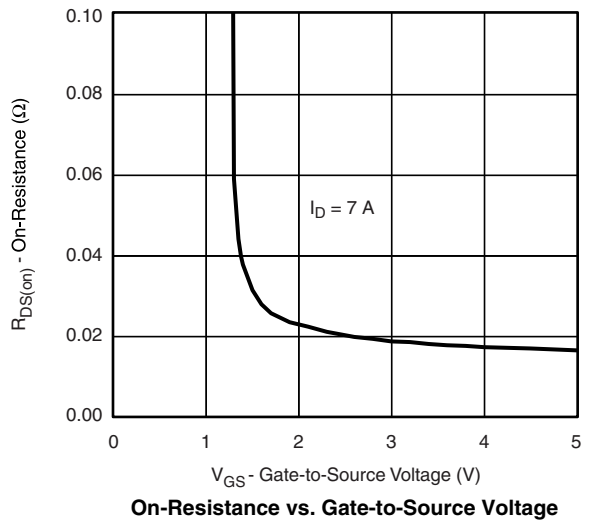
**Gate Charge**



**On-Resistance vs. Junction Temperature**

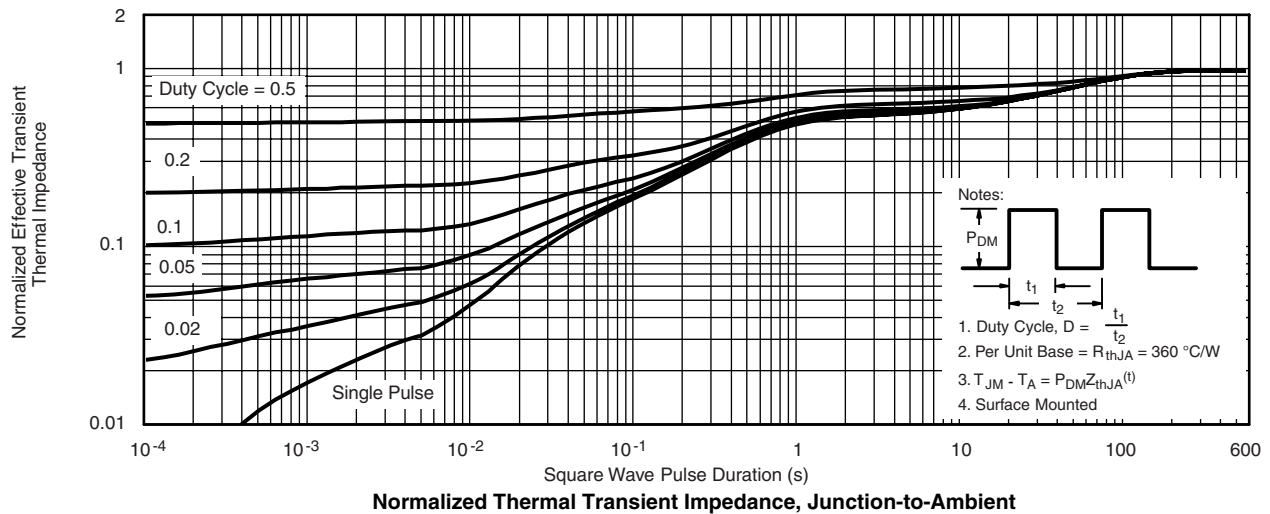
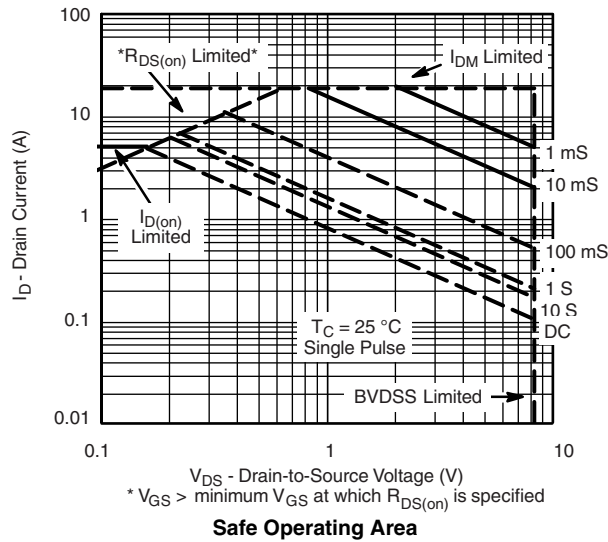
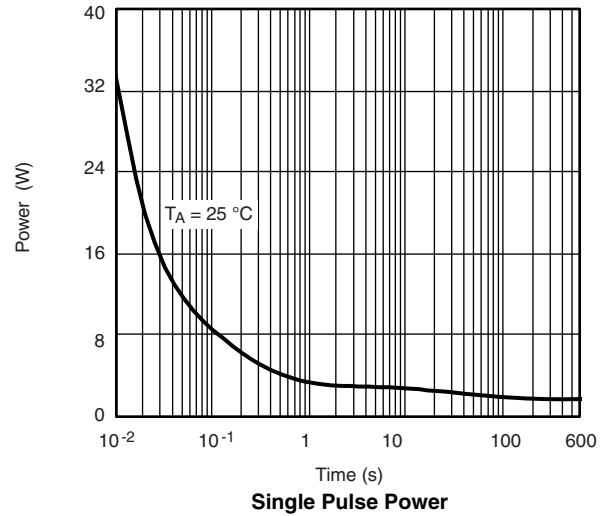
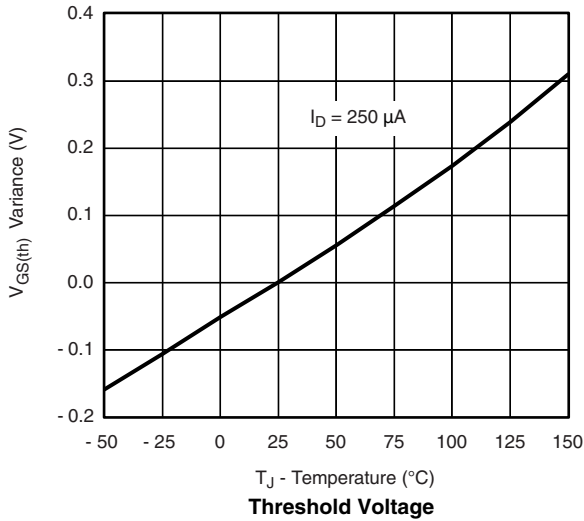


**Source-Drain Diode Forward Voltage**

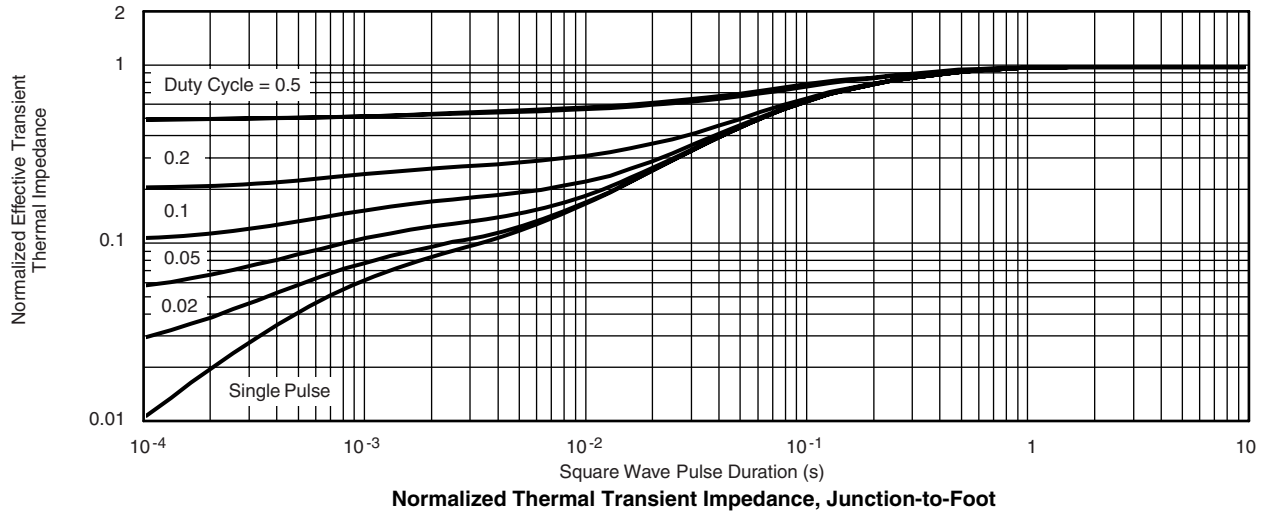


**On-Resistance vs. Gate-to-Source Voltage**

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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